

TO-251/TO-252 DMOS

• $V_{GS(th)} = 2 \text{ to } 4\text{V}$

N Channel

(Volts) Min	Device		$I_{DS(on)}$ Max (mA)	I_D (Amps) Max	P_D (Watts) Max
	TO-251	TO-252	$V_{GS} = 10\text{V}$		
60	NDU506A	NDD506A	50	19	72
	NDU506AE	NDD506AE			
	NDU506B	NDD506B	60	18	72
	NDU506BE	NDD506BE			
	NDU406A	NDD406A	100	15	40
	NDU406AE	NDD406AE			
	NDU406B	NDD406B	150	12	40
	NDU406BE	NDD406BE			
	MTD3055E1	MTD3055E	150	8	20

TO-251/TO-252 Logic Level DMOS

• $V_{GS(th)} = 1 \text{ to } 2\text{V}$

N Channel

(Volts) Min	Device		$I_{DS(on)}$ Max (mA)	I_D (Amps) Max	P_D (Watts) Max
	TO-251	TO-252	$V_{GS} = 10\text{V}$		
60	NDU506AL	NDD506AL	50	19	72
	NDU506AEL	NDD506AEL			
	NDU506BL	NDD506BL	60	18	72
	NDU506BEL	NDD506BEL			
	NDU406AL	NDD406AL	100	15	40
	NDU406AEL	NDD406AEL			
	NDU406BL	NDD406BL	150	12	40
	NDU406BEL	NDD406BEL			
	MTD3055EL1	MTD3055EL	180	12	40

Note: Suffix E indicates the device is avalanche energy rated.

